

Tanmoy Das

List of Publications by Year in descending order

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Version: 2024-02-01

24
papers

1,039
citations

758635

12
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676716

22
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26
all docs

26
docs citations

26
times ranked

2315
citing authors

#	ARTICLE	IF	CITATIONS
1	Graphene-Based Flexible and Stretchable Electronics. <i>Advanced Materials</i> , 2016, 28, 4184-4202.	11.1	537
2	Graphene-based flexible and wearable electronics. <i>Journal of Semiconductors</i> , 2018, 39, 011007.	2.0	76
3	Lithography-free plasma-induced patterned growth of MoS ₂ and its heterojunction with graphene. <i>Nanoscale</i> , 2016, 8, 15181-15188.	2.8	68
4	Surface-Functionalization-Mediated Direct Transfer of Molybdenum Disulfide for Large-Area Flexible Devices. <i>Advanced Functional Materials</i> , 2018, 28, 1706231.	7.8	66
5	Highly Flexible Hybrid CMOS Inverter Based on Si Nanomembrane and Molybdenum Disulfide. <i>Small</i> , 2016, 12, 5720-5727.	5.2	46
6	Atomic layer deposited (TiO ₂) _x (Al ₂ O ₃) _{1-x} /In _{0.53} Ga _{0.47} As gate stacks for III-V based metal-oxide-semiconductor field-effect transistor applications. <i>Applied Physics Letters</i> , 2012, 100, 062905.	1.5	30
7	Doping-Free All PtSe ₂ Transistor via Thickness-Modulated Phase Transition. <i>ACS Applied Materials & Interfaces</i> , 2021, 13, 1861-1871.	4.0	30
8	Sputter-Deposited La ₂ O ₃ on p-GaAs for Gate Dielectric Applications. <i>Journal of the Electrochemical Society</i> , 2011, 159, G15-G22.	1.3	28
9	Interface Properties of Atomic Layer Deposited TiO ₂ /Al ₂ O ₃ Films on In _{0.53} Ga _{0.47} As/InP Substrates. <i>ACS Applied Materials & Interfaces</i> , 2014, 6, 3263-3274.	4.0	24
10	Development of electronic devices based on two-dimensional materials. <i>FlatChem</i> , 2017, 3, 43-63.	2.8	23
11	Effects of Ti incorporation on the interface properties and band alignment of HfTaO _x thin films on sulfur passivated GaAs. <i>Applied Physics Letters</i> , 2011, 98, 022901.	1.5	19
12	Tunable Current Transport in PdSe ₂ via Layer-by-Layer Thickness Modulation by Mild Plasma. <i>Advanced Electronic Materials</i> , 2020, 6, 2000008.	2.6	17
13	An extension of the Curie-von Schweidler law for the leakage current decay in MIS structures including progressive breakdown. <i>Microelectronics Reliability</i> , 2011, 51, 1535-1539.	0.9	12
14	Degradation analysis and characterization of multifilamentary conduction patterns in high-field stressed atomic-layer-deposited TiO ₂ /Al ₂ O ₃ nanolaminates on GaAs. <i>Journal of Applied Physics</i> , 2012, 112, 064113.	1.1	12
15	Vertical field effect tunneling transistor based on graphene-ultrathin Si nanomembrane heterostructures. <i>2D Materials</i> , 2015, 2, 044006.	2.0	12
16	Surface Passivation of GaAs Substrates with SiO ₂ Deposited Using ALD. <i>Electrochemical and Solid-State Letters</i> , 2011, 14, G52.	2.2	10
17	Polarity Control and Weak Fermi-Level Pinning in PdSe ₂ Transistors. <i>ACS Applied Materials & Interfaces</i> , 2021, 13, 43480-43488.	4.0	9
18	Interface Properties of Mixed (TiO ₂) _x (Y ₂ O ₃) _{1-x} and (Ta ₂ O ₅) _x (Y ₂ O ₃) _{1-x} Gate Dielectrics on Sulfur-Passivated GaAs. <i>Journal of the Electrochemical Society</i> , 2012, 159, H323-H328.	1.3	7

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19	Gate- Controlled Rectifying Direction in PdSe ₂ Lateral Heterojunction Diode. Advanced Electronic Materials, 2021, 7, 2100005.	2.6	5
20	Thermal stability of HfO _x Ny gate dielectrics on p-GaAs substrates. Semiconductor Science and Technology, 2010, 25, 125009.	1.0	4
21	Electrical properties and noise characterization of HfO ₂ gate dielectrics on strained SiGe layers. Thin Solid Films, 2012, 522, 267-273.	0.8	3
22	Degradation and breakdown characteristics of Al/HfYO _x /GaAs capacitors. Thin Solid Films, 2012, 520, 2956-2959.	0.8	1
23	Studies on Lattice vibration, impurity and defects in MIS structures using Hf-based dielectrics on Si and SiGe substrates. , 2012, , .		0
24	Flexible Electronics: Highly Flexible Hybrid CMOS Inverter Based on Si Nanomembrane and Molybdenum Disulfide (Small 41/2016). Small, 2016, 12, 5650-5650.	5.2	0